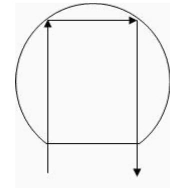
Part Number Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	WaferVendor
	2.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Type	P	Wafer Vendor
	6.0	Dopant	Boron	Wafer Vendor
	7.0	Resistivity	1 - 20 ohm cm	Wafer Vendor
	8.0	Overall Thickness	500.00 +/- 25.00 um	Wafer Vendor
	9.0	Total Thickness Variation (TTV)	<10.00um	Guaranteed by process
	10.0	Orientation	<100> +/-1.0	Wafer Vendor
	11.0	Bow	<50.00um	ADE measuremnet
	12.0	Warp	<50.00um	ADE measuremnet
	13.0	Back Surface Quality	Polished	Wafer Vendor
	14.0	Front Surface Quality	Prime	Wafer Vendor
	15.0	Edge Chips	None	Bright Light 100% (note 2)
DeviceSilicon	16.0	Haze	None	Bright Light, 100% (note 2).
	17.0	Scratches	None	Bright Light, 100% (note 2).
	18.0	Device Field Oxidation	3,000.00 +/- 150.00 A	Nanospec centre point, 4%
HandleSilicon	19.0	Handle Thickness	500.00 +/- 25.00 um	Wafer Vendor

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

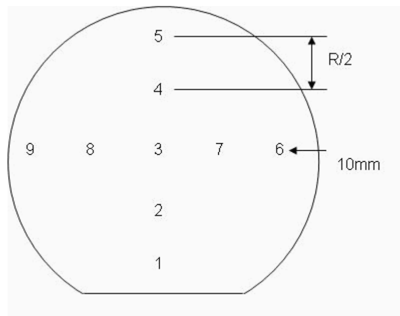
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information